

Rubrene on mica: from the early growth stage to late crystallization

G. Hlawacek¹, X. He¹, C. Teichert¹,
S. Abd al-Baqi², H. Sitter²

1) Institute of Physics, University of Leoben, A-8700 Leoben, Austria
2) Institute of Semiconductor and Solid State Physics, University of Linz, A-4040 Linz, Austria



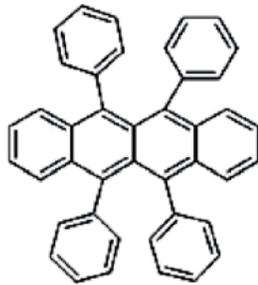
Motivation

Rubrene shows a high hole mobility in single crystals. However, Rubrene thin films exhibit a much lower mobility. Recent work on Rubrene thin films on weakly interacting amorphous SiO₂ showed that the formed crystalline structures can increase the thin film mobility drastically [1,2].

Here, we present a detailed atomic-force microscopy (AFM) study on Rubrene thin films on the stronger interacting crystalline mica(001) surface. The evolution of the initial growth stage and peculiarities in the growth rate are analyzed. For these initial layers of amorphous Rubrene the wetting behaviour is investigated as a function of deposition temperature. Finally, the morphology of the crystalline spherulites, developing in thick films is shown.

Experimental

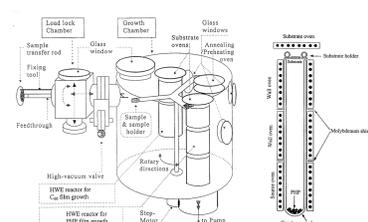
Rubrene



- Tetracene core
- p-type semiconductor
- single crystal mobility of 15 cm²/Vs
- difficult to grow thin films
 - very low mobility 10⁻⁶ cm²/Vs
- Amorphous phase not stable against O₂
- High stability of crystalline phase

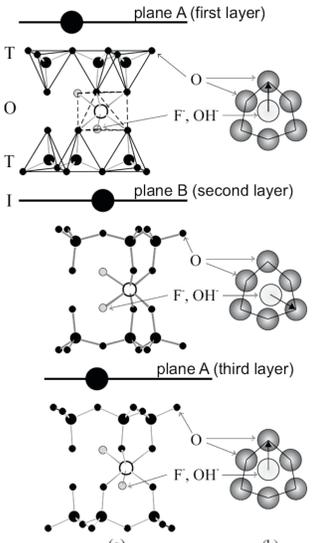
Hot Wall Epitaxy

- Deposition temperature: 363 K to 393 K
- Base pressure: 1x10⁻⁶ mbar
- Source temperature: 453 K to 508 K
- Wall temperature: 453 K to 508 K
- Deposition rate: roughly 25nm/h

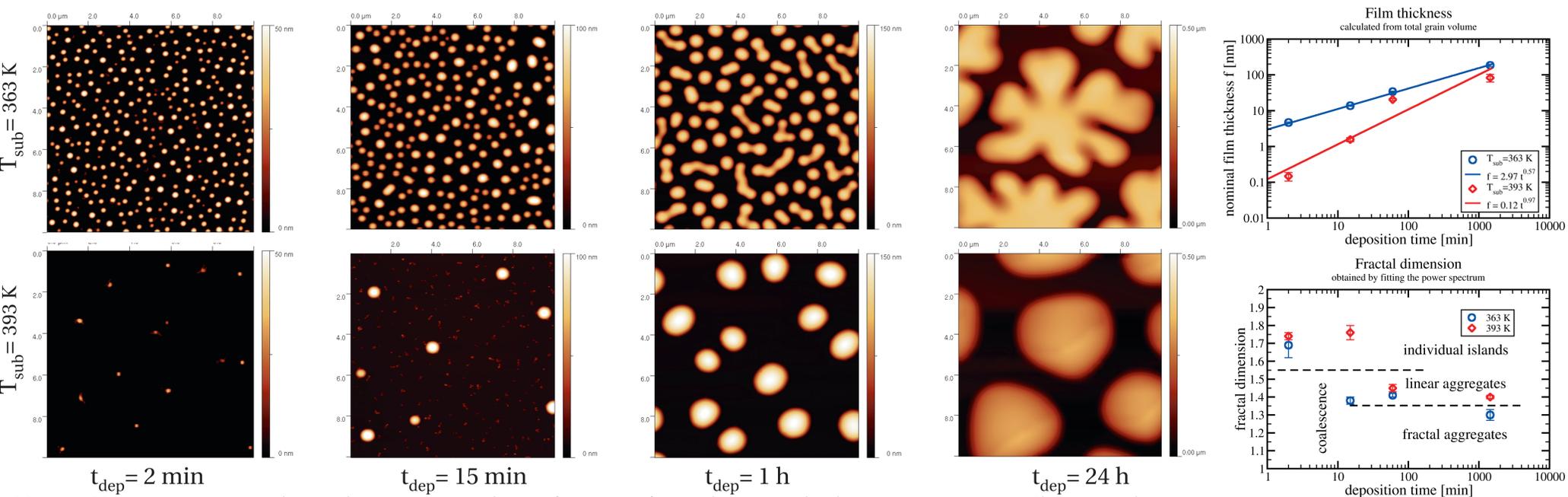


Mica(001)

The mica(001) surface used is a cleavage plane of 2M₁-muscovite with the formula KAl₂(AlSi₃)O₁₀(OH,F)₂. Due to charge repulsion between the oxygen in the top most layer the anions are displaced from the center of the hexagonal opening - which leads to a two fold symmetry of mica(001) and a strong surface dipol.

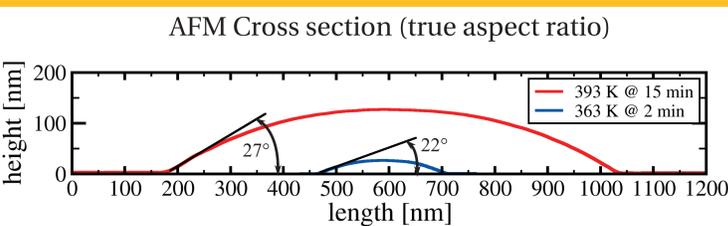


Morphological analysis



10 μm x 10 μm AFM images obtained in tapping mode as a function of growth time and substrate temperature. Please note the different height scales. Morphological evolution: Circular islands -> coalescence -> larger fractal islands

Contact angle of Rubrene on mica(001)

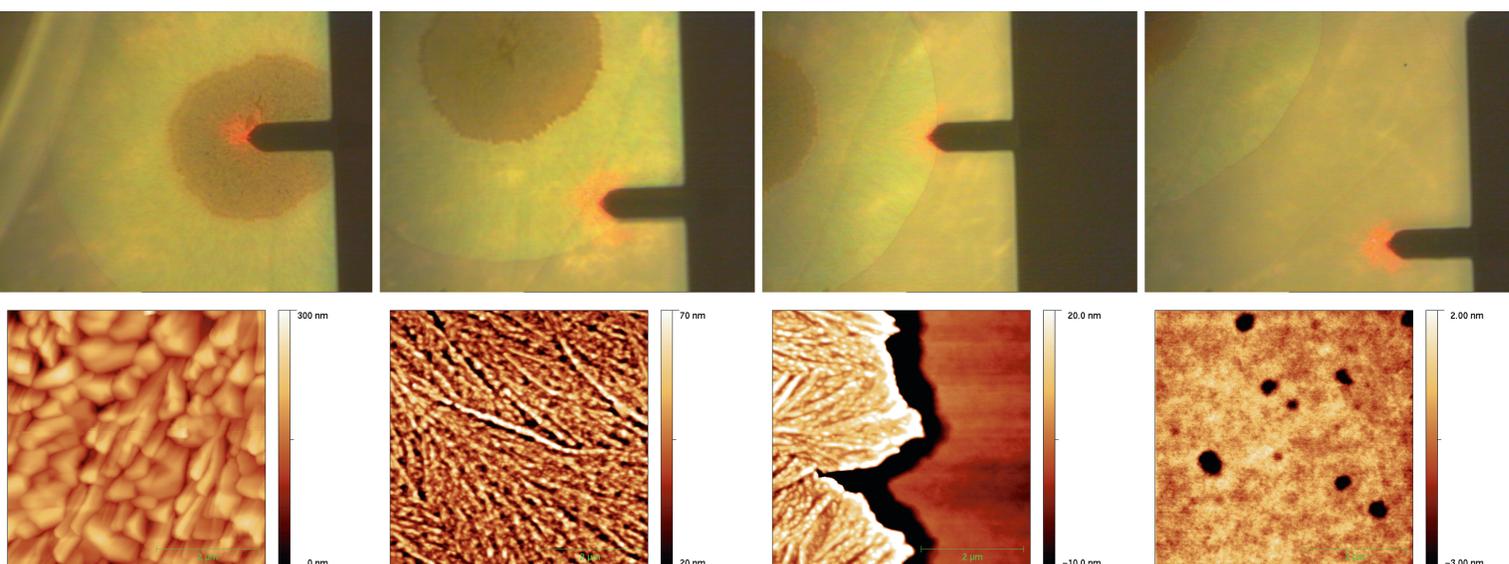


T _{sub}	Contact angle
363 K	22°
393 K	27°

- With increasing T_{sub} the contact angle increases
- System gets more rubrenophobic
- Surf. energy of Rubrene increases stronger with increasing T_{sub} then surf. energy of mica.

- Higher coverage at 363 K
 - P_{stick}(363 K) > P_{stick}(393 K)
- Sublinear growth rate at 363 K
 - P_{stick}(Rub./Rub.) < P_{stick}(Rub./mica)
- Fractal dimension D calculated from power spectra [3]
- Fractal analysis allows separation into three stages
 - growth of individual islands: D > 1.5
 - begin of coalescence: 1.35 > D > 1.5
 - formation of branched islands: D < 1.35

Formation of crystalline spherulites



- Optical microscopy images (top row) of thicker films show crystalline spherulites embedded in a transparent amorphous matrix.
- T_{dep}=90°C, T_{source}=235°C (corresponds to a higher growth rate)
- Center: faceted large crystals showing a slight radial structure
- Iris: typical branched dendritic growth, strong radial structure
- Edge: deep gap between crystalline spherulite and matrix
- Outer region: amorphous film with some holes a few nm deep

Summary

- Initial growth**
 - Amorphous islands start to coalesce with increasing coverage.
 - The sticking coefficient depends on temperature and is different on mica and on Rubrene.
 - Wettability of Rubrene on mica(001) decreases with increasing T_{sub}.
- Later growth stage**
 - Formation of crystalline spherulites in an amorphous matrix.
 - The spherulite center is formed by large faceted crystallites.
 - The iris is characterized by branched dendritic crystallites with a strong radial structure.

References

- [1] Y. Luo, et al., Phys. stat. sol. a 204 (2007) 1851.
- [2] C. H. Hsu, et al., Appl. Phys. Lett. 91 (2007) 193505.
- [3] A. Mannelquist, et al., Appl. Phys. A 66 (1998) 891.

Contact

Gregor Hlawacek (gregor.hlawacek@unileoben.ac.at) Christian Teichert (teichert@unileoben.ac.at)
Institute of Physics
University of Leoben, 8700 Leoben, Austria
web: <http://www.unileoben.ac.at/~spmgroup/>
Supported by Austrian Science Fund Projects S9707 and S9706